



EMA5001 Lecture 7

Short-Circuit Diffusion, & Reaction Diffusion



Diffusion Along Grain Boundaries (1)

□ Diffusion along grain boundaries or surface also follow Arrhenius Equation

$$D_b = D_{b0} \exp\left(-\frac{Q_b}{RT}\right)$$

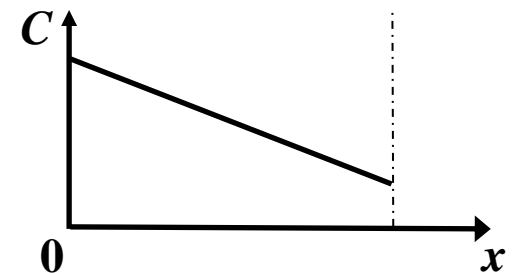
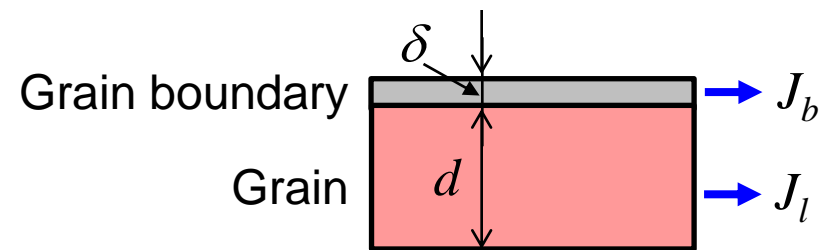
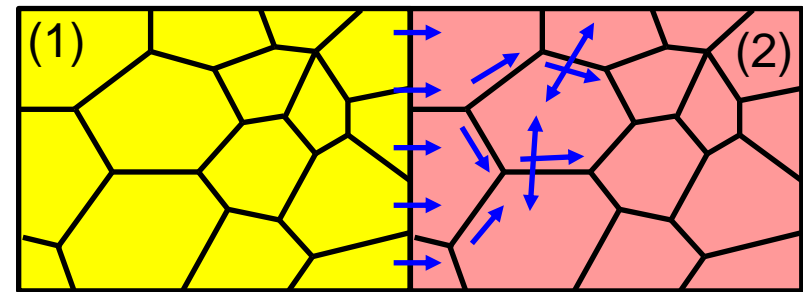
$$D_s = D_{s0} \exp\left(-\frac{Q_s}{RT}\right)$$

□ Relationship of lattice (bulk), grain boundaries, and surface diffusion

$$D_s > D_b > D_l$$

□ Example

- Steady state diffusion through a thin polycrystalline sheet
- Grain boundary perpendicular to sheet
- Concentration gradient identical in grain boundaries and in lattice





Diffusion Along Grain Boundaries (2)

□ Continue from p.10

Flux through lattice: $J_l = -D_l \frac{dC}{dx}$

Flux through the grain boundary $J_b = -D_b \frac{dC}{dx}$

If grain size of d ,

If grain boundaries has effective thickness of δ , and $\delta \ll d$

Total flux

$$J = \frac{J_l d + J_b \delta}{d + \delta} \approx \frac{J_l d + J_b \delta}{d} = \frac{1}{d} \cdot \left(-D_l \frac{dC}{dx} d - D_b \frac{dC}{dx} \delta \right)$$

Therefore,

$$J = - \left(D_l + \frac{\delta}{d} D_b \right) \cdot \frac{dC}{dx}$$

For diffusion through such a polycrystalline film, the apparent diffusion coefficient

$$D_{app} = D_l + \frac{\delta}{d} D_b$$



Diffusion Along Grain Boundaries (3)

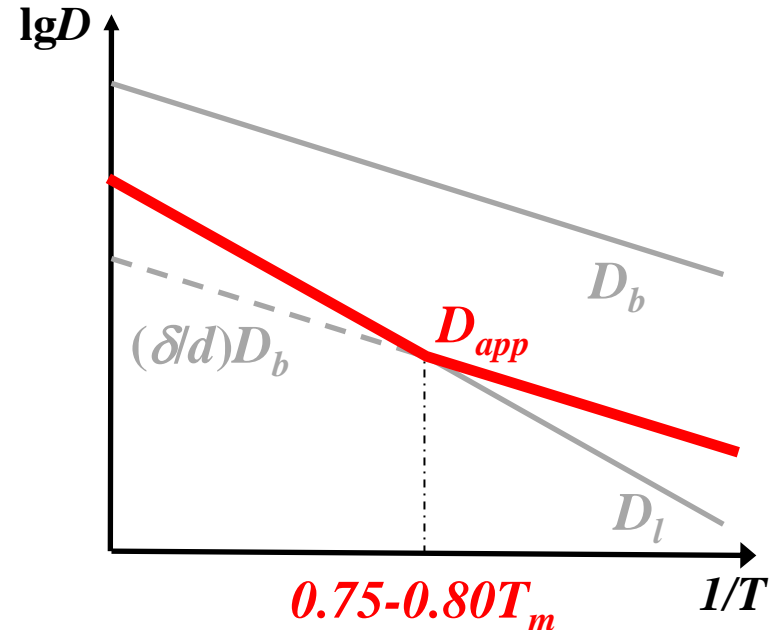
□ Continue from p.11

$$D_{app} = D_l + \frac{\delta}{d} D_b$$

Or

$$\frac{D_{app}}{D_l} = 1 + \frac{\delta D_b}{d D_l}$$

- The relative importance of lattice and grain diffusion depends on ratio of $\delta D_b / d D_l$
- Normally
 - $D_b > D_l$
 - $Q_b \cong 0.5 Q_l$
- Temperature effect
 - Grain boundary diffusion dominates at low T;
 - Lattice diffusion dominates at high T
 - Transition temperature of $0.75-0.80 T_m$
- More pronounced for material w/ small grains
- Grain boundary diffusion depends on specific boundary and even direction





Diffusion Along Dislocations

□ Diffusion along dislocation is often also faster than lattice diffusion

▪ $Q_d \cong 0.5 Q_l$

Flux through lattice: $J_l = -D_l \frac{dC}{dx}$

Flux through the dislocation $J_d = -D_d \frac{dC}{dx}$

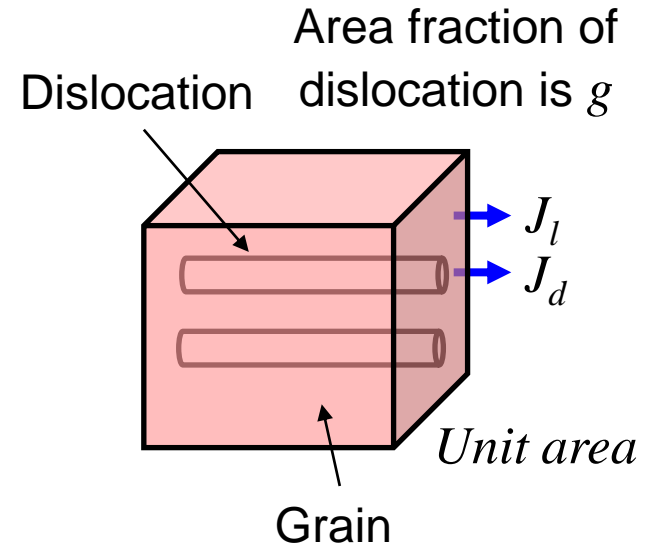
If area fraction of total dislocation is g , ($g \sim 10^{-7}$)

Total flux

$$J = J_l + J_d g = -D_l \frac{dC}{dx} - g D_d \frac{dC}{dx} = -(D_l + g D_d) \frac{dC}{dx}$$

$$D_{app} = D_l + g D_d$$

$$\frac{D_{app}}{D_l} = 1 + g \frac{D_d}{D_l}$$





Diffusion Involving Two Phases - with Interfacial Reactions

□ In binary system involving 2 phases, if

- Slow diffusion process
- Fast interfacial process \rightarrow local equilibrium
- Fast phase transformation at the phase boundary

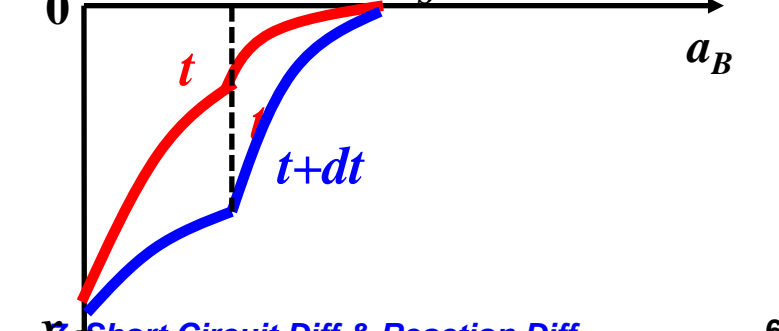
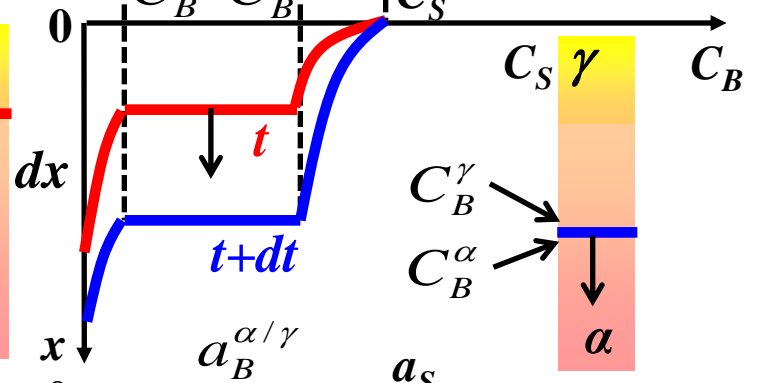
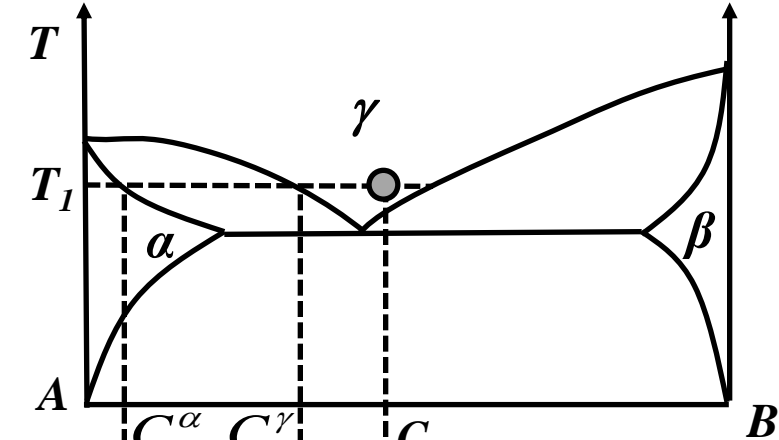
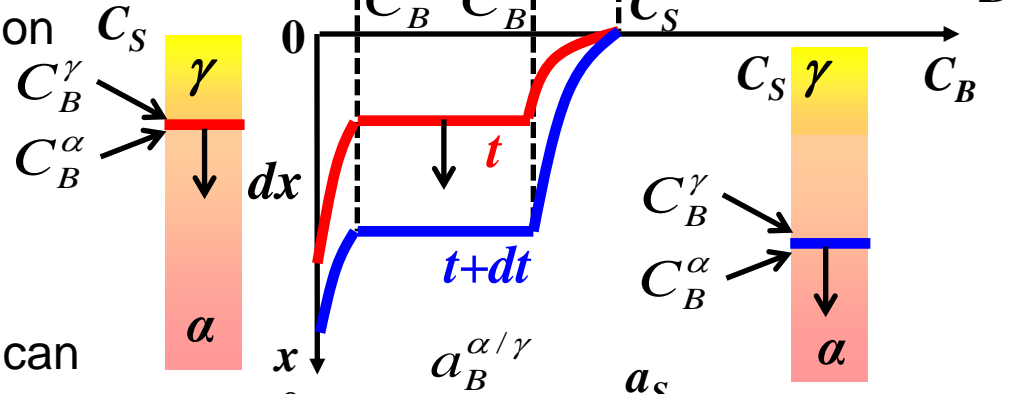
□ Phase analysis

Binary alloy, fixed surface concentration of C_S . The number of phases can be present:

$$f = c - p + 2$$

At constant temperature of T_I ,

- Single phase region: composition can change
- At two phase boundary, composition will be fixed





Rate of Interface Movement if Controlled by Diffusion

□ For reaction diffusion

In a very short time dt , interface between α and γ moves from x to $x + dx$.

The change in B within dx is

$$\delta_B = (C_B^\gamma - C_B^\alpha) dx$$

From flux point of view, the change in B is

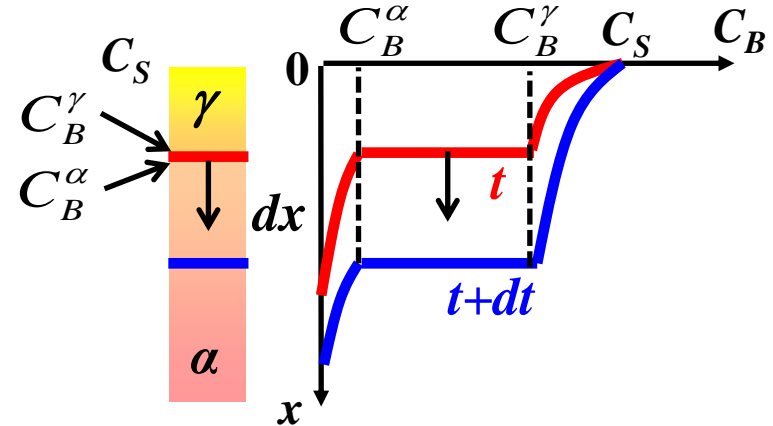
$$\delta_B = \left(-\tilde{D}_\gamma \frac{\partial C}{\partial x} \Big|_{C_B^\gamma} dt \right) - \left(-\tilde{D}_\alpha \frac{\partial C}{\partial x} \Big|_{C_B^\alpha} dt \right) = \left[\tilde{D}_\alpha \frac{\partial C}{\partial x} \Big|_{C_B^\alpha} - \tilde{D}_\gamma \frac{\partial C}{\partial x} \Big|_{C_B^\gamma} \right] dt$$

Therefore,

$$\frac{dx}{dt} = \frac{1}{C_B^\gamma - C_B^\alpha} \cdot \left[\tilde{D}_\alpha \frac{\partial C}{\partial x} \Big|_{C_B^\alpha} - \tilde{D}_\gamma \frac{\partial C}{\partial x} \Big|_{C_B^\gamma} \right]$$

Introduce $\lambda = \frac{x}{\sqrt{t}}$

$$\frac{\partial C}{\partial x} = \frac{dC}{d\lambda} \cdot \frac{\partial \lambda}{\partial x} = \frac{dC}{d\lambda} \cdot \frac{\partial \left(\frac{x}{\sqrt{t}} \right)}{\partial x} = \frac{1}{\sqrt{t}} \cdot \frac{dC}{d\lambda}$$





Rate of Interface Movement if Controlled by Diffusion

□ Continue from p. 15

$$\frac{\partial C}{\partial x} = \frac{1}{\sqrt{t}} \cdot \frac{dC}{d\lambda}$$

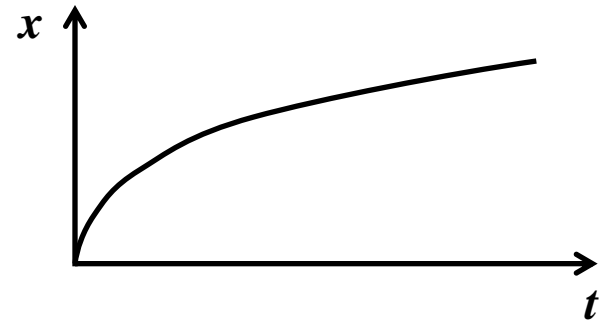
Because the concentration in each phase at the interface are constant, $\frac{dC}{d\lambda}$ is a constant depending on concentration

$$\frac{dx}{dt} = \frac{1}{C_B^\gamma - C_B^\alpha} \cdot \left[\tilde{D}_\alpha \frac{\partial C}{\partial x} \Big|_{C_B^\alpha} - \tilde{D}_\gamma \frac{\partial C}{\partial x} \Big|_{C_B^\gamma} \right]$$

Therefore,

$$\frac{dx}{dt} = A'(C) \frac{1}{\sqrt{t}}$$

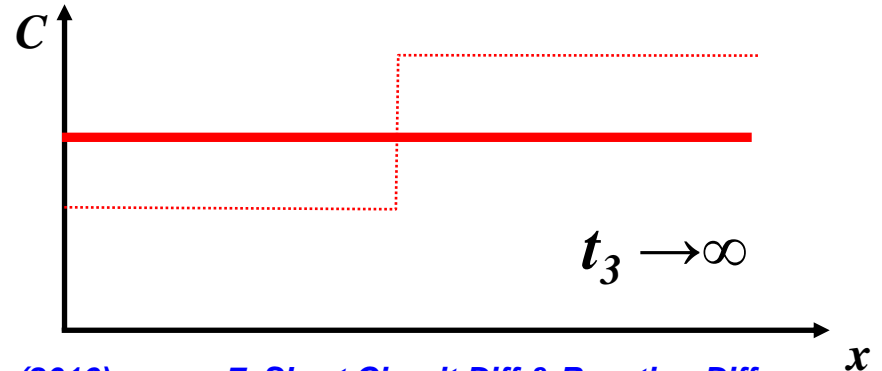
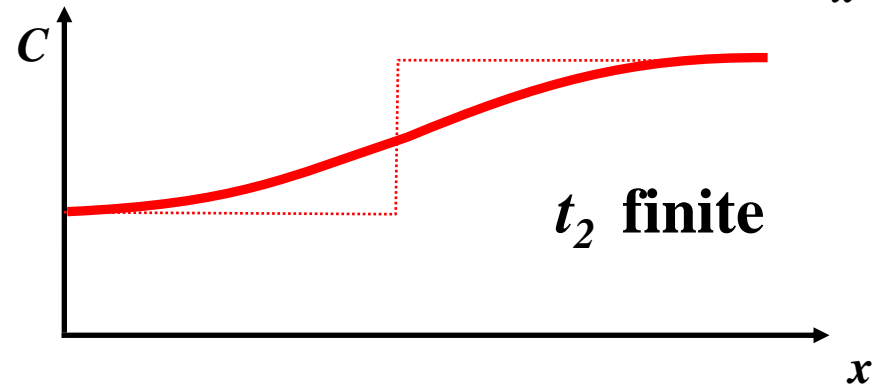
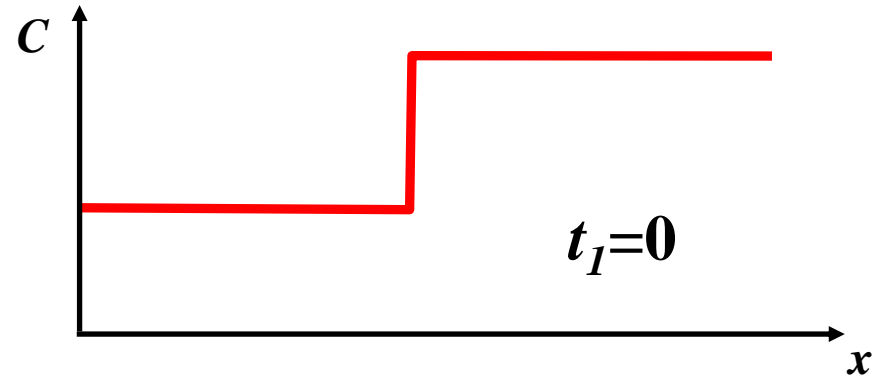
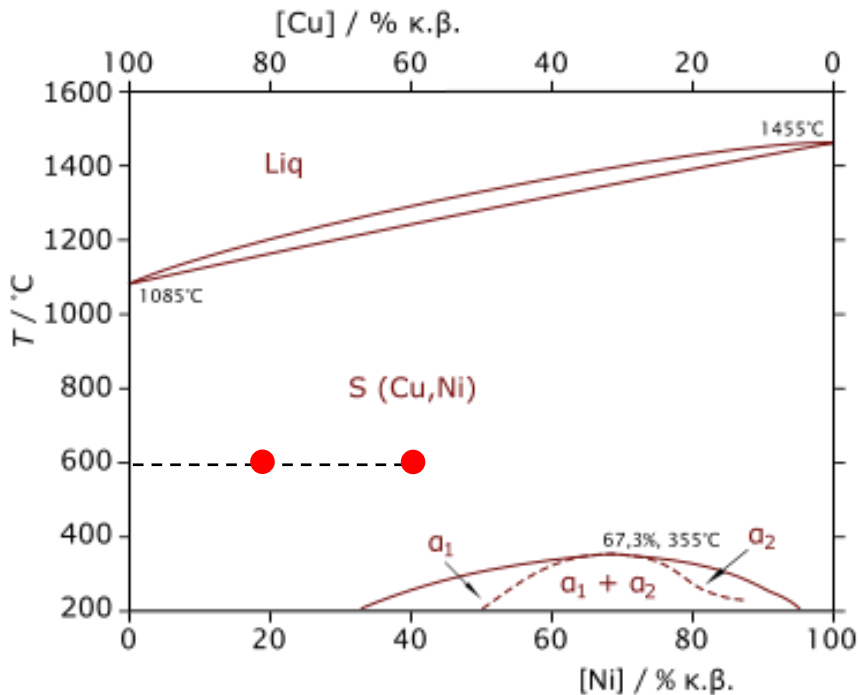
Integrate on both sides, we have $x = B'(C)\sqrt{t}$
 $x^2 = B(C)t$





Concentration Profile Change for Diffusion involving Single Phase

- Two pieces of Ni-Cu alloys with different initial compositions put in close contact at elevated temperature, plot the change of concentration profile for i) $t_1 = 0$, ii) t_2 finite, iii) $t_3 \rightarrow \infty$

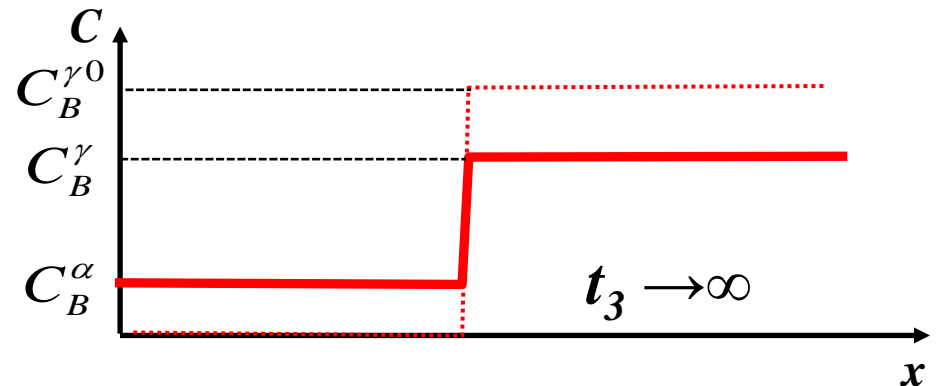
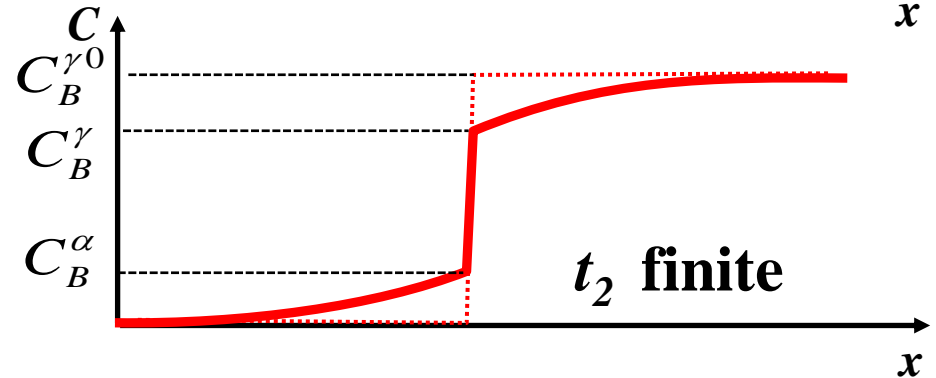
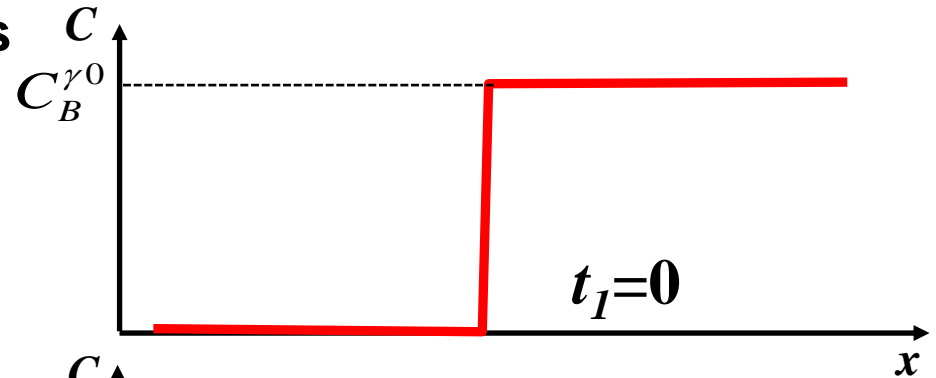
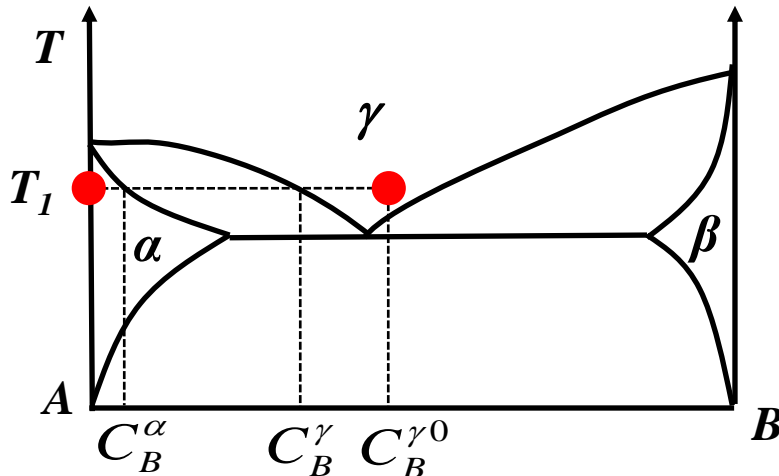




Concentration Profile Change for Diffusion involving Two-Phases (1)

Two pieces of similar sized alloys with different composition and phases (one is α with pure A and the other is γ) are put in close contact at elevated temperature, as below.

Assuming slow diffusion and local equilibrium at interface
 Please plot concentration profile for i) $t_1 = 0$, ii) t_2 finite, iii) $t_3 \rightarrow \infty$



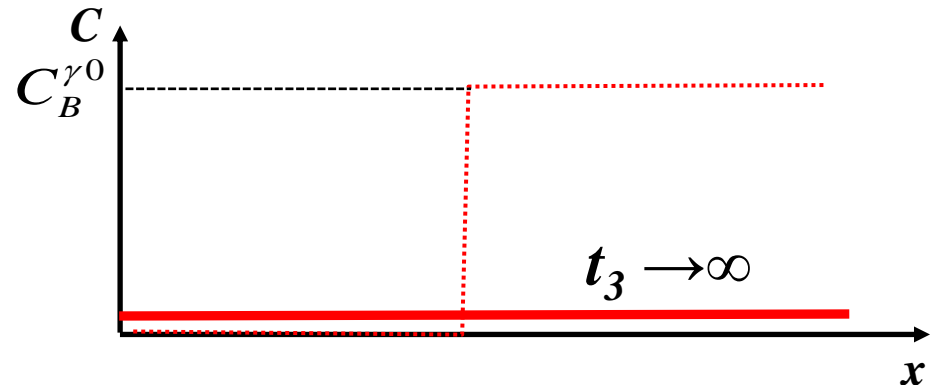
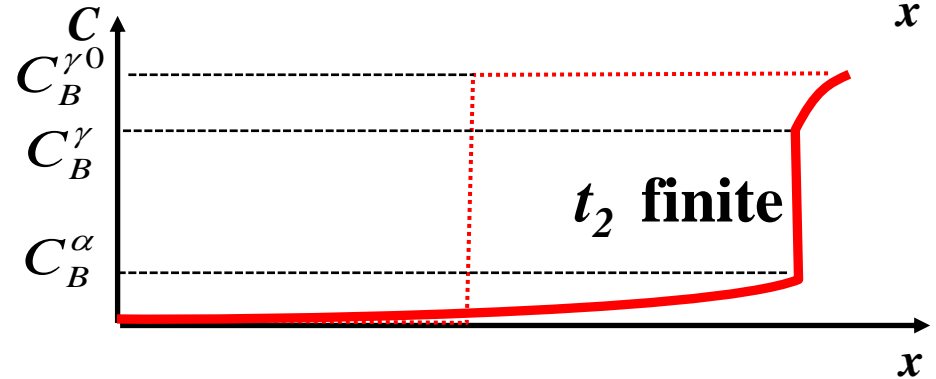
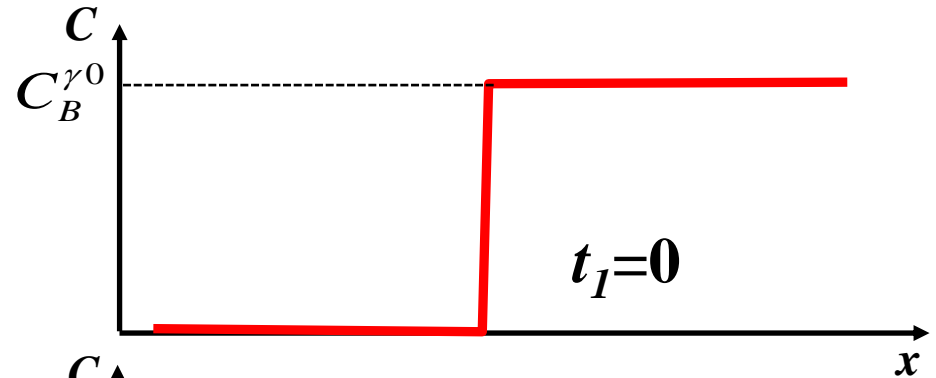
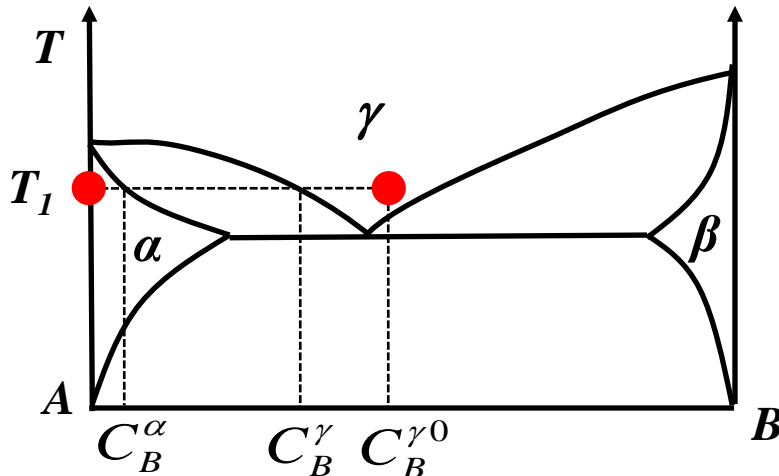


Concentration Profile Change for Diffusion involving Two-Phases (2)

□ A very large piece of one is α with pure A and a very small piece of γ are put in close contact at elevated temperature, as below.

Assuming slow diffusion and local equilibrium at interface

Please plot concentration profile for i) $t_1 = 0$, ii) $t_2 \text{ finite}$, iii) $t_3 \rightarrow \infty$





Homework

- Porter 3rd Ed, Exercise 2.7
- Due **Feb 29** class